

# Analog BOSA



## Feature

- 1270nm/1330nm DFB laser diode and APD chip
- Low threshold current and 6G bandwidth.
- High intensity of light emission
- High coupling efficiency and Fiber output high power
- Very good Linearity

## Application

- Analog transmission system and 6G RF transceiver
- High speed and Big data processing
- AI Network

## Absolute Maximum Ratings

Parameter		Min.	Max.	Unit
Tx	Power Voltage (LD)	--	3.6	V
	Reverse Voltage (LD)	--	2	V
	Forward Current (LD)	--	120	mA
	Reverse Voltage (MPD)	--	20	V
	Forward Current (MPD)	--	2	mA
Rx	Reverse Voltage	--	15	V
	Forward Current (LD)	--	10	mA
	Input Power	--	5	dBm

Threshold Voltage	200	--	V
Storage Temperature	-40	+85	°C
Operating Temperature	0	+75	°C
Lead Soldering Temperature	--	260/10	°C/s

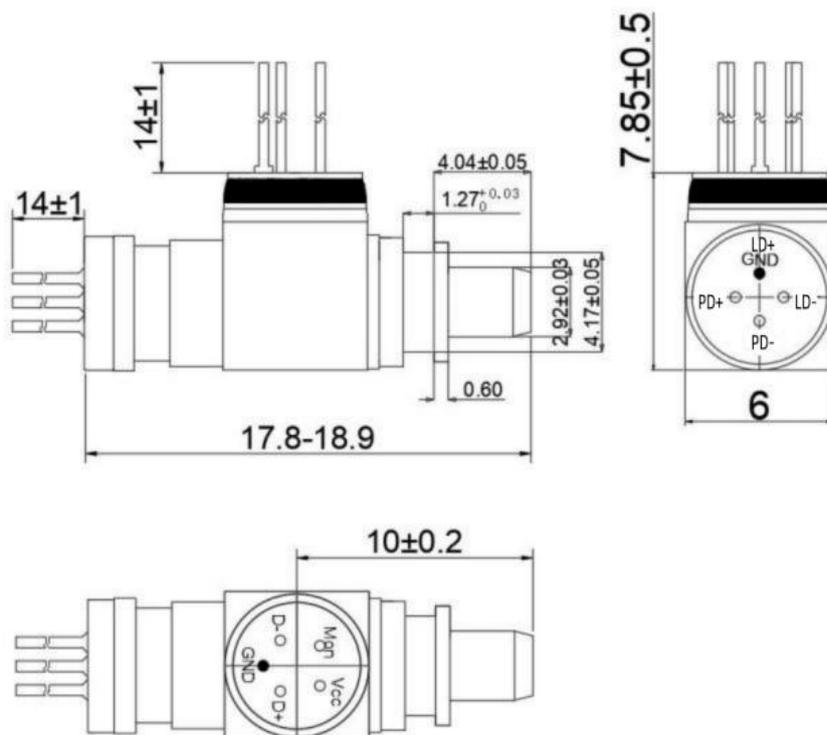
## Optical and Electrical Characteristics

Parameter	Symbol	SPEC.				Test Conditions
		Min.	Typ.	Max.	Unit	
Central Wavelength	$\lambda_c$	1260	1270	1280	nm	$I_{op} = 50 \sim 60 \text{mA}$
	$\lambda_c$	1320	1330	1340	nm	$I_{op} = 50 \sim 60 \text{mA}$
Fiber Output Power	Pf	6.0	--	10.0	mW	$I_{op} = I_{th} + 20 \text{mA}$ , CW,
Threshold Current	Ith	5	--	15	mA	Tc=25°C
		1	--	40	mA	Tc=0~+75°C
Spectral Width (-20dB)	$\Delta\lambda$	--	--	1	nm	$I_{op} = I_{th} + 20 \text{mA}$ , Tc=25°C
Slope Efficiency	$\eta$	0.2	--	--	W/A	
Side-mode suppression ratio	SMSR	30	--	--	dB	$I_{op} = I_{th} + 20 \text{mA}$ , Tc=25°C
Monitor Current	I <sub>m</sub>	50	--	1000	μA	Tc=0~+75°C
Monitor Dark Current	I <sub>d</sub>	--	--	200	nA	Tc=0~+75°C
RF Parameter						
Bandwidth (3dB)	BW	0.01	--	7	GHz	
Input P-1dB	--	15	--	--	V	5GHz
2nd Harmonic Rejection	--	40	--	--	dBc	Pin=0dBm, 100MHz~4GHz
		30	--	--	dBc	Pin=0dBm, 4GHz~6GHz
Working Condition						
Power Voltage	--	3.135	--	3.465	V	
Operating Current	I <sub>op</sub>	--	--	80	mA	
Operating Voltage	V <sub>cc</sub>	--	--	1.6	V	

## Electrical and optical characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	TEST CONDITIONS
Power Supply	V <sub>CC</sub>	4.750	--	5.250	V	
Operating Wavelength	$\lambda$	1320	1330	1340	nm	
		1260	1270	1280	nm	
Responsivity	R <sub>e</sub>	0.8	--	--	mA/mW	
APD dark current	I <sub>d</sub>	--	--	300	nA	
Breakdown voltage	V <sub>BR</sub>	20	--	43	V	Dark current, I <sub>d</sub> =10 $\mu$ A
Bandwidth (3dB down)	BW	0.01	--	7	GHz	
Overload	Ps	6	--	---	dBm	
Return Loss	RL	--	--	35	dB	
2nd Harmonic Rejection	--	38	--	--	dBc	100MHz~1GHz,Input=2dBm
3rd Harmonic Rejection	--	53	--	--	dBc	100MHz~1GHz,Input=2dBm
ESD Requirement	ESD	200	--	--	V	

## Package Dimensions and Pin Description(LC)



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